

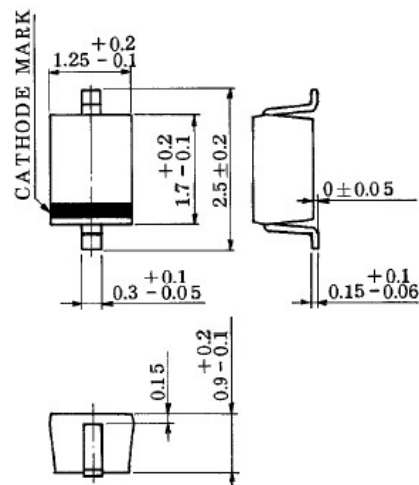
VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

VCO FOR UHF BAND RADIO

- Ultra Low Series Resistance : $r_s = 0.2\Omega$ (Typ.)
- Useful for Small Size Set

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	15	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 125$	$^\circ\text{C}$

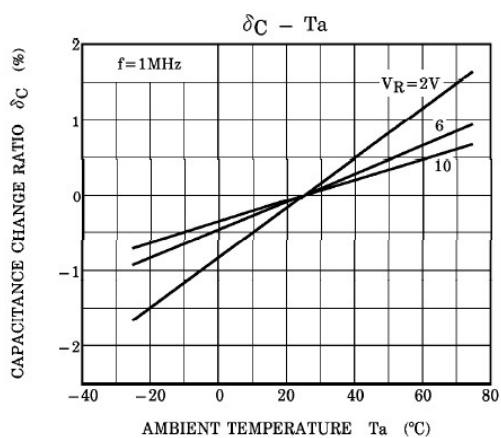
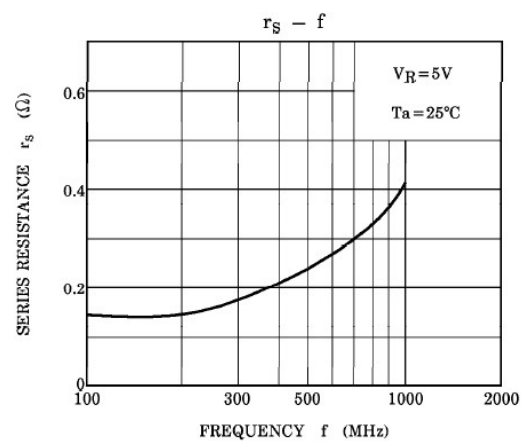
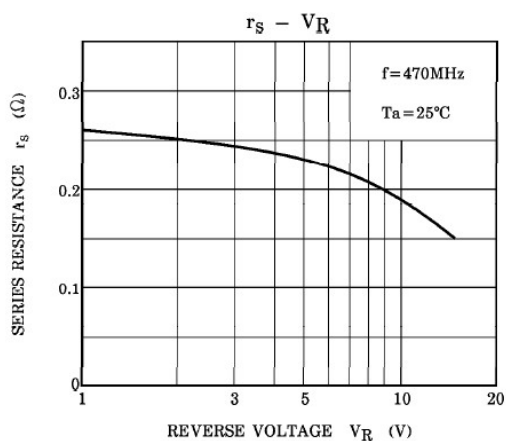
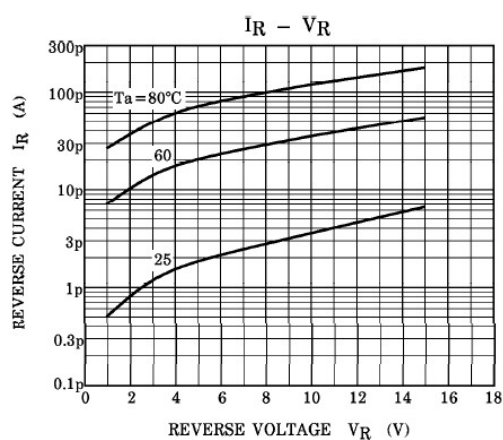
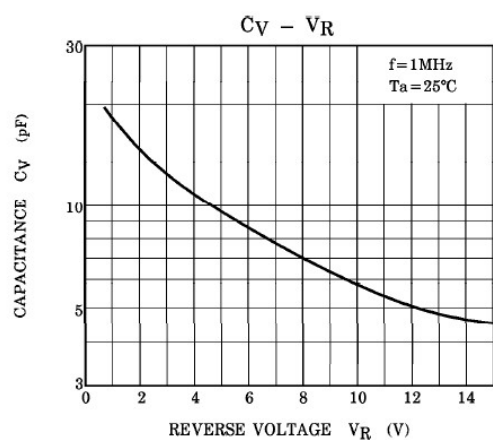


Weight : 0.004g

Unit in mm

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 1\mu\text{A}$	15	—	—	V
Reverse Current	I_R	$V_R = 15\text{V}$	—	—	5	nA
Capacitance	C_{2V}	$V_R = 2\text{V}, f = 1\text{MHz}$	14	15	16	pF
Capacitance	C_{10V}	$V_R = 10\text{V}, f = 1\text{MHz}$	5.5	6	6.5	pF
Capacitance Ratio	C_{2V} / C_{10V}	—	2.0	2.5	—	—
Series Resistance	r_s	$V_R = 5\text{V}, f = 470\text{MHz}$	—	0.2	0.4	Ω



NOTE : $\delta C (\%) = \frac{C(T_a) - C(25^\circ\text{C})}{C(25^\circ\text{C})} \times 100$